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7	16	-	-	us 6348731	20020219		Copper interconnections with enhanced electromigration resistance and		257/7521
<u> </u>	١			El	<u>.</u>		reduced defect sensitivity and method of founding same		2574.7684
∭ r	ŀ	r	6	US	50031106		Method for improving nucleation and adhesion of CVD and ALO films		257/762:
:::	. .		:	20000205823			deposited onto low-dielectric-constant dielectrics		257/E21. 204/252;
3 r.:	1	: [05	20040923	52	Monolithic fuel cell structure and method of manufacture		429/35
	1	100		20040185923	20040205	177	Davice structure for closely spaced electrodes		205/777.
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	†:::			US	20030703	:3)	Detection of Alox ears for process control in FeRAM processing	:438/238	25?/E2:.
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∭ r.	-	٦	~	us 6713342	20040330	135	FeRAM sidewall miffusion barrier etch	438/239	
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34		ng me		SA	20030731		FERAM CAPACITOR FOST STACK ETCH CLEAN/REPAIR	438/240	257/E21.
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#	1			US 6492222	20021210	13.9	Method of dry etching PRT capacitor stack to form high-density	438/240	408/2092
∭ ¹.	,	1		E1	<u>;</u>	1	ferroelectric memory devices		438/250/
		3.		US	20040506	15	Etch-scop material for improved manufacture of magnetic devices	438/3	
3				26646687037	1		to the second of	438/3	257/821.
∭ r-	٠,	٣.	~	US	20030710		Method of forming an FeRAN capacitor having a bottom electrode diffusion	430/3	2.717 521.
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